

**Session Program**

**20-22 Nov 2017**

**31st RD50 Workshop (CERN)**

***Defects and material characterisation***

CERN, 6/2-024 - BE Auditorium Meyrin  
6-2-024

# Monday 20 November

13:30

## Defects and material characterisation

**Session** | **Location:** CERN, 6/2-024 - BE Auditorium Meyrin, 6-2-024 | **Convener:** Michael Moll

13:30–13:50

### Photoconductivity and magnetoresistance mobility in the irradiated to 1015-1017 cm<sup>-2</sup> neutron fluence Si

**Speaker**

Prof. Juozas Vaitkus

13:50–14:10

### TLM method for active doping profile evaluation

**Speaker**

Prof. ABDENOUR LOUNIS

14:10–14:30

### Study of point- and cluster-defects in radiation-damaged silicon

**Speaker**

Joern Schwandt

14:30–14:50

### Study of the ionizing energy depositions after fast neutron interactions in silicon

**Speakers**

Benedikt Ludwig Bergmann, Stanislav Pospisil

14:50–15:10

### Electrically active defects in 4H-SiC

**Speaker**

Dr Ivana Capan

15:10–15:30

### Update on NitroStrip project

**Speaker**

Marta Baselga Bacardit

15:30–16:00

### Coffee Break

16:00–16:20

### Acceptor removal in silicon pad diodes with different resistivities

**Speakers**

Mr Pedro Goncalo Dias De Almeida, Yana Gurinskaya, Isidre MATEU

16:20–16:40

### TSC Measurements of Acceptor Removal

**Speaker**

Yana Gurinskaya

16:40–17:10

### Discussion

**Speakers**

Ioana Pintilie, Michael Moll

17:10